

HMBT5401

High Voltage PNP Transistor

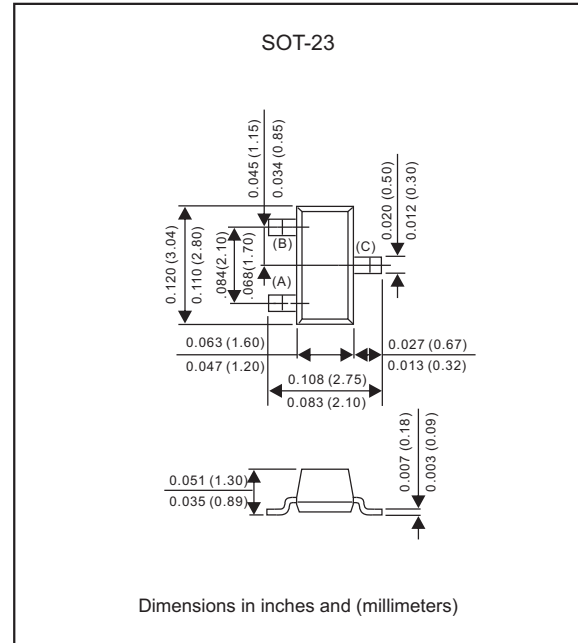
Package outline

Features

- Lead-free parts for green partner, exceeds environmental standards of MIL-STD-19500 /228

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-23
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.008 gram



Maximum ratings (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	Value	UNIT
Collector -Base Voltage		V_{CBO}	-160	Vdc
Collector -Emitter Voltage		V_{CEO}	-150	Vdc
Emitter -Base Voltage		V_{EBO}	-5.0	Vdc
Collector Current - Continuous		I_C	-500	mAdc

Thermal Characteristics

Characteristics	CONDITIONS	Symbol	Max	UNIT
Total device dissipation FR-5 board (1)	$T_A = 25^\circ\text{C}$	P_D	225	mW
	Derate above 25°C	P_D	1.8	mW/ $^\circ\text{C}$
Thermal resistance	Junction to ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total device dissipation alumina substrate(2)	$T_A = 25^\circ\text{C}$	P_D	300	mW
	Derate above 25°C	P_D	2.4	mW/ $^\circ\text{C}$
Thermal resistance	Junction to ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Operating temperature		T_J	-55 ~ +150	$^\circ\text{C}$
Storage temperature		T_{STG}	-55 ~ +150	

1.FR-5 = 1.0 X 0.75 X0.062 in.

2.Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.

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ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-160			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C =-1mA, I _B =0	-150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-120V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)} *	V _{CE} =-5V, I _C =-1mA	80			
	h _{FE(2)} *	V _{CE} =-5V, I _C =-10mA	100		300	
	h _{FE(3)} *	V _{CE} =-5V, I _C =-50mA	50			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =-10mA, I _B =-1mA			-0.2	V
	V _{CE(sat)2}	I _C =-50mA, I _B =-5mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C =-10mA, I _B =-1mA			-1	V
	V _{BE(sat)2}	I _C =-50mA, I _B =-5mA			-1	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=30MHz	100			MHz

*Pulse test: pulse width ≤300μs, duty cycle ≤ 2.0%.

Small-Signal characteristics

PARAMETER	CONDITIONS	Symbol	Min.	Max.	UNIT
Current-Gain-Bandwidth Product	I _C = -10mA dc, V _{CE} = -10V dc, f = 100MHz	f _T	100	300	MHZ
Output Capacitance	V _{CB} = -10V dc, I _E = 0, f = 1.0MHz	C _{obo}		6.0	pF
Small Signal Current Gain	I _C = -1.0mA dc, V _{CE} = -10V dc, f = 1.0KHz	h _{fe}	40	200	-
Noise Figure	I _C = -200μA dc, V _{CE} = -5.0V dc, R _s = 10Ω, f = 1.0KHz	NF		8.0	dB

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FIG.1 DC Current Gain

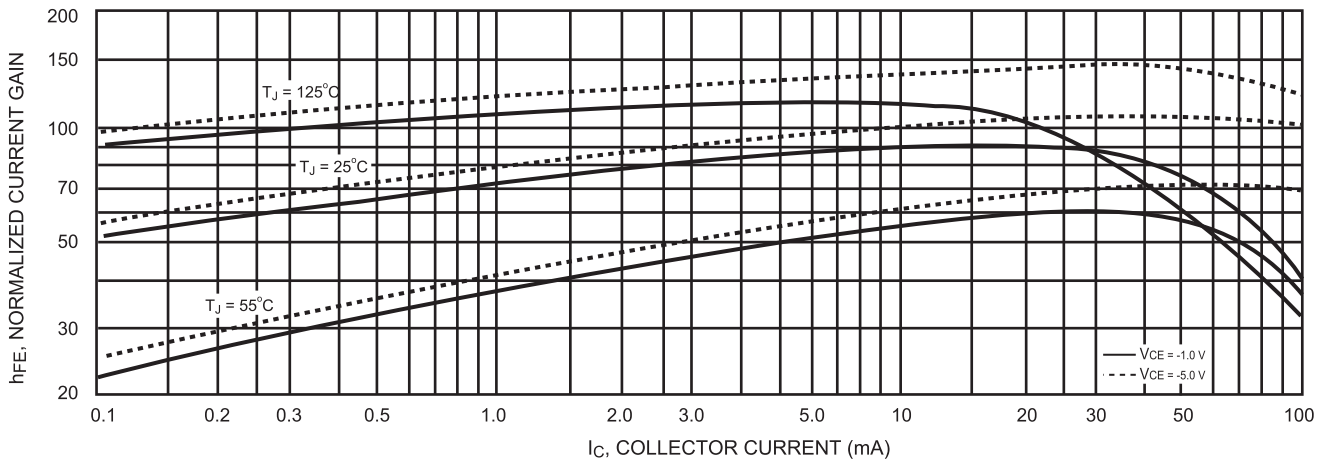


FIG.2 Collector Saturation Region

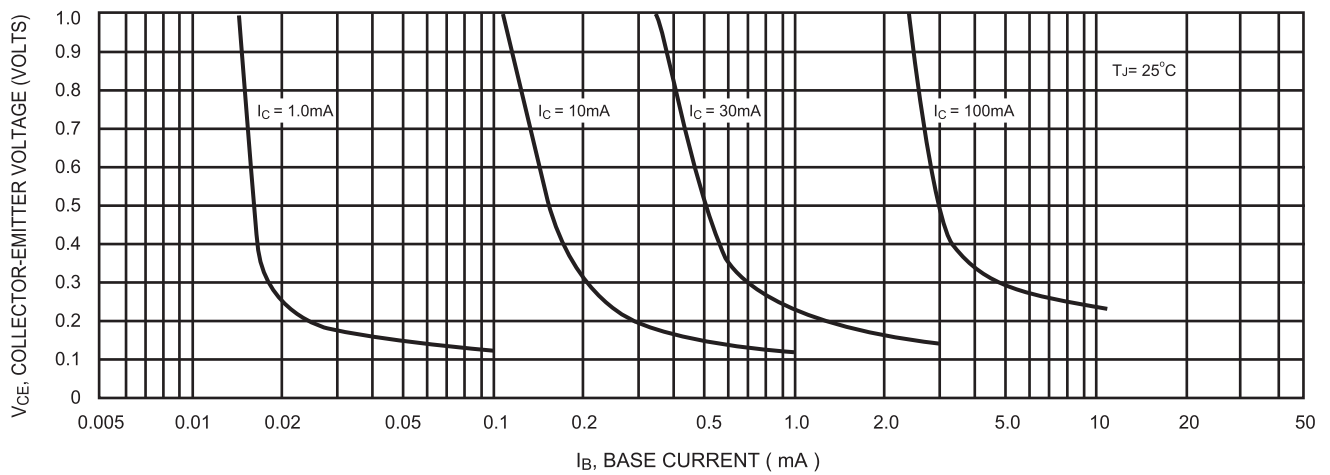


FIG.3 Temperature Coefficients

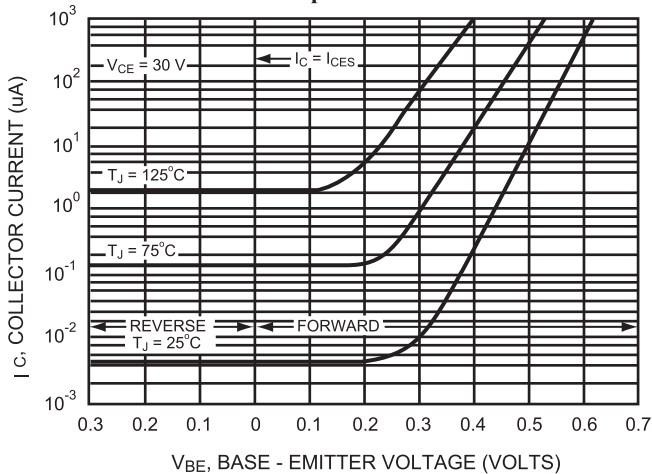
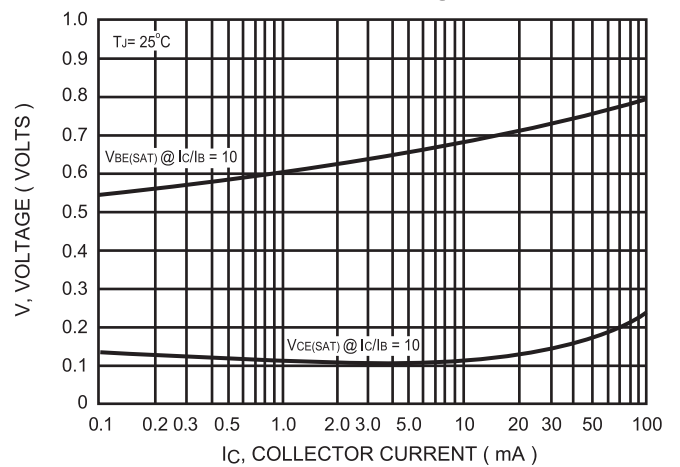


FIG.4 " On " Voltages



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FIG.5 Temperature Coefficients

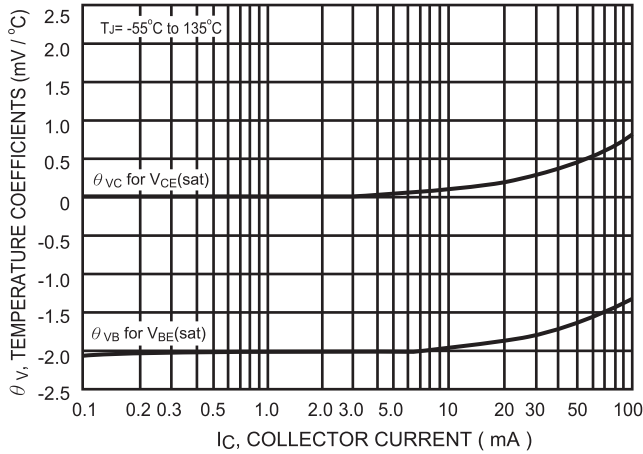
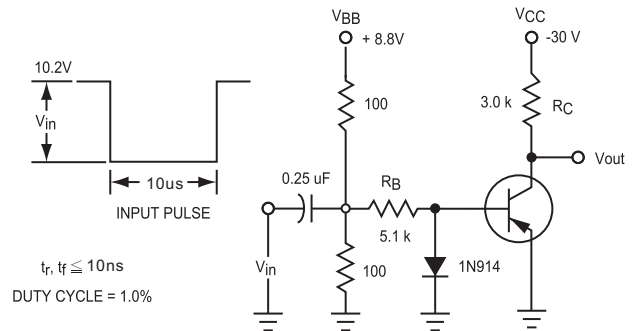


FIG.6 Switching Time Test Circuit



VALUES SHOWN ARE FOR I_C @ 10 mA

FIG.7 Capacitances

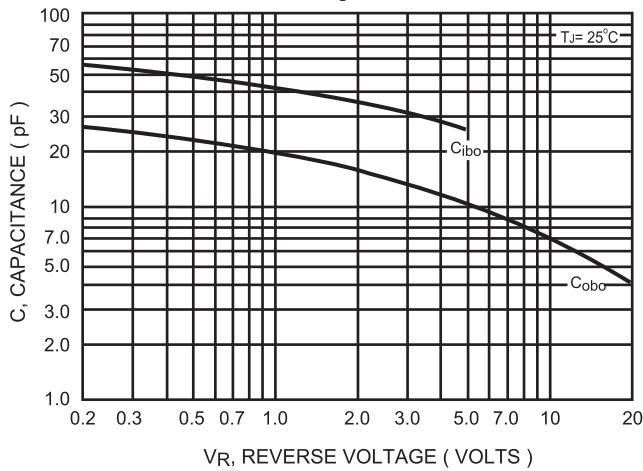


FIG.8 Turn - On Time

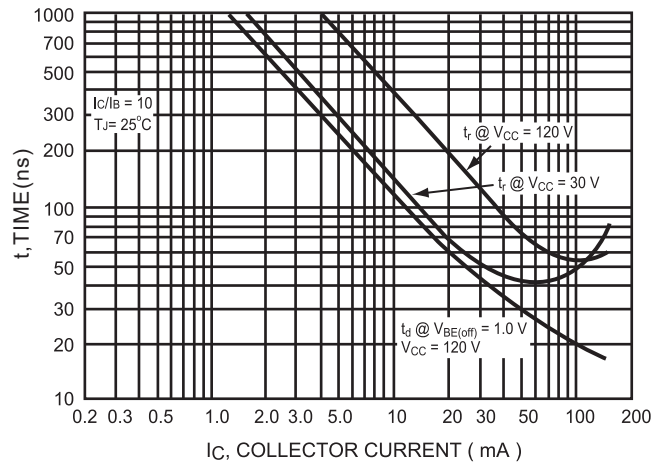
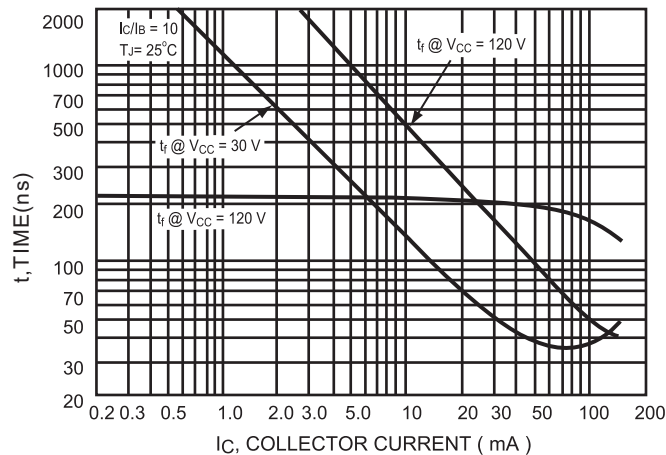
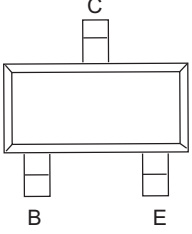
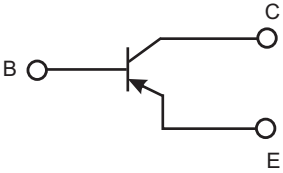


FIG.9 Turn - Off Time



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Pinning information

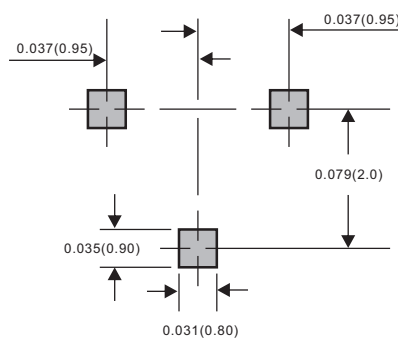
Pin	Simplified outline	Symbol
PinB Base PinC Collector PinE Emitter		

Marking

Type number	Marking code
HMBT5401	2L

Suggested solder pad layout

SOT-23



Dimensions in inches and (millimeters)